



ZXMN2A03E6

#### **Product Summary**

V <sub>(BR)</sub> dss	RDS(ON) Max	I <sub>D</sub> T <sub>A</sub> = +25°C
20V	$55m\Omega @ V_{GS} = 4.5V$	4.6A
200	$100m\Omega @ V_{GS} = 2.5V$	3.4A

#### Description

This new generation MOSFET is designed to minimize the on-state resistance ( $R_{DS(ON)}$ ) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

# Applications

- DC-DC Converters
- Power Management Functions
- Backlighting

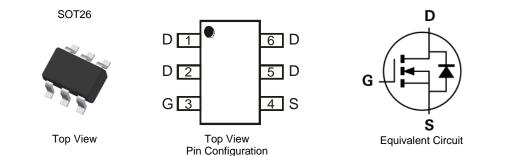
#### 20V N-CHANNEL ENHANCEMENT MODE MOSFET

#### **Features and Benefits**

- Low Input Capacitance
- Low On-Resistance
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

### **Mechanical Data**

- Case: SOT26
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Tin Finish Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208 (€3)
- Weight: 0.018 grams (Approximate)



## Ordering Information (Note 4)

Part Number	Case	Packaging
ZXMN2A03E6TA	SOT26	3,000/Tape & Reel

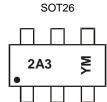
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

# **Marking Information**



2A3 = Product Type Marking Code YM = Date Code Marking Y or  $\overline{Y}$  = Year (ex: C = 2015) M or  $\overline{M}$  = Month (ex: 9 = September)

Date Code Key

Notes:

Year	2015		2016	2017		2018	2019		2020	2021		2022
Code	С		D	E		F	G		Н	I		J
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



# **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DSS</sub>	20	V
Gate-Source Voltage	V <sub>GSS</sub>	±12	V
Continuous Drain Current, V <sub>GS</sub> = 10V	I <sub>D</sub>	4.6 3.7 3.7	А
Maximum Body Diode Forward Current (Note 6)	IS	2.7	A
Pulsed Drain Current (Note 7)	I <sub>DM</sub>	16	A
Pulsed Source Current (Note 7)	I <sub>SM</sub>	16	A

#### **Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation Linear Derating Factor	T <sub>A</sub> = +25°C (Note 5)	PD	1.1 8.8	W mW/°C
Total Power Dissipation Linear Derating Factor	T <sub>A</sub> = +25°C (Note 6)	PD	1.7 13.6	W mW/°C
Thermal Resistance, Junction to Ambient	Steady State (Note 5)	Devi	113	°C/W
mermai Resistance, sunction to Ambient	Steady State (Note 6)	R <sub>0JA</sub>	70	°C/W
Operating and Storage Temperature Range	T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C	

#### Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	20	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	IDSS		_	1	μA	$V_{DS} = 20V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>		_	±100	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)	•		•		•	·	
Gate Threshold Voltage	V <sub>GS(TH)</sub>	0.7	_		V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance (Note 8)	P		—	55	mΩ	$V_{GS} = 4.5V, I_D = 7.2A$	
Static Drain-Source On-Resistance (Note 6)	R <sub>DS(ON)</sub>		—	100	11152	$V_{GS} = 2.5V, I_D = 4.6A$	
Diode Forward Voltage (Note 8)	V <sub>SD</sub>		0.85	0.95	V	$V_{GS} = 0V, I_{S} = 4.1A$	
Forward Transconductance (Notes 8 & 10)	<b>g</b> fs		13		S	V <sub>DS</sub> = 10V, I <sub>D</sub> = 7.2A	
DYNAMIC CHARACTERISTICS (Note 10)					•	·	
Input Capacitance	C <sub>iss</sub>		837				
Output Capacitance	Coss		168	_	pF	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 0V f = 1.0MHz	
Reverse Transfer Capacitance	Crss	_	90	_		1 - 1.00012	
Total Gate Charge	Qg		8.2	_			
Gate-Source Charge	Q <sub>gs</sub>		2.3	_	nC	$V_{DS} = 10V, I_D = 7.2A, V_{GS} = 4.5V$	
Gate-Drain Charge	Q <sub>gd</sub>		2.0	_			
Turn-On Delay Time	t <sub>D(ON)</sub>		4.7	_			
Turn-On Rise Time	t <sub>R</sub>		5.7	_	ns	$V_{GS} = 4.5V, V_{DD} = 10V, R_G = 6.0\Omega,$	
Turn-Off Delay Time	t <sub>D(OFF)</sub>		18.5		115	I <sub>D</sub> = 1.0A	
Turn-Off Fall Time	tF		10.5		]		
Body Diode Reverse Recovery Time	t <sub>RR</sub>		12		ns	I <sub>F</sub> = 1.9A, dl/dt = 100A/µs	
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>		4.9	_	nC	$T_{F} = 1.9A$ , $u/u_{L} = 100A/\mu_{S}$	

Notes: 5. For a device surface mounted on 25mm x 25mm FR-4 PCB with high coverage of single sided 1oz copper, in still air conditions.

6. For a device surface mounted on FR-4 PCB measured at t  $\leq$ 5 secs.

7. Repetitive rating 25mm x 25mm FR-4 PCB, D = 0.05, pulse width 10µs - pulse width limited by maximum junction temperature. Refer to Transient Thermal Impedance graph.

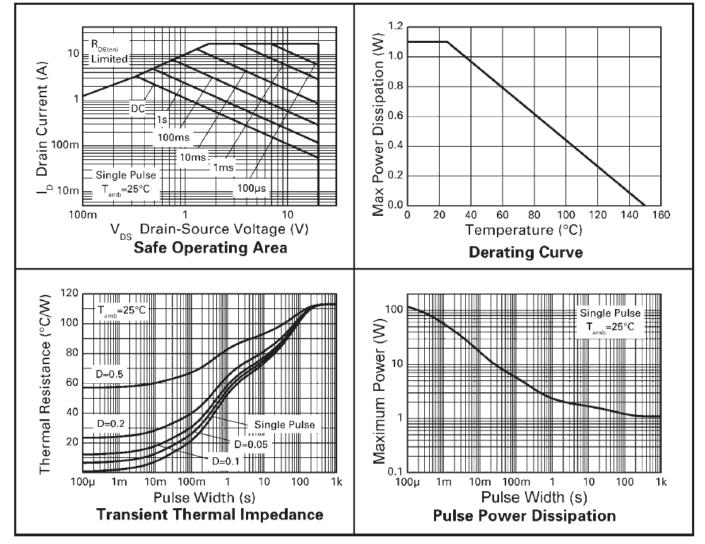
8. Measured under pulsed conditions. Width=300 $\mu$ s. Duty cycle  $\leq$  2%.

9. Short duration pulse test used to minimize self-heating effect.

10. Guaranteed by design. Not subject to product testing.

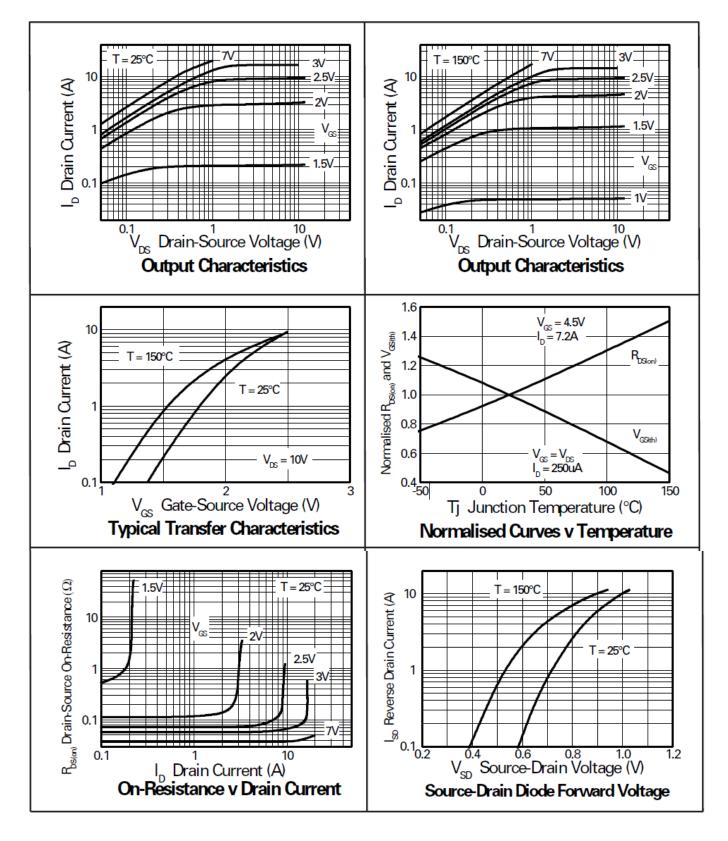


## **TYPICAL CHARACTERISTICS**



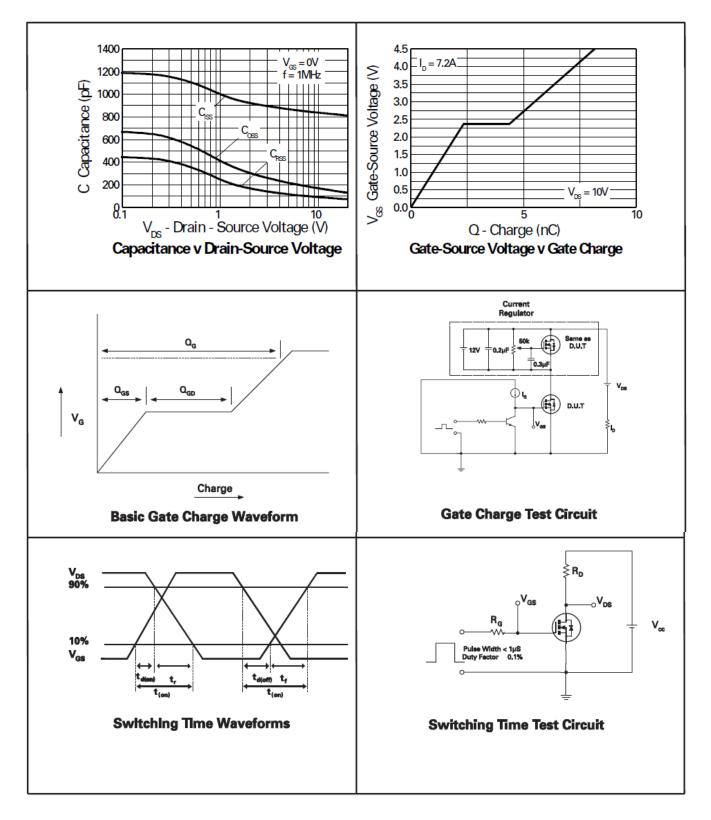


# **TYPICAL CHARACTERISTICS**





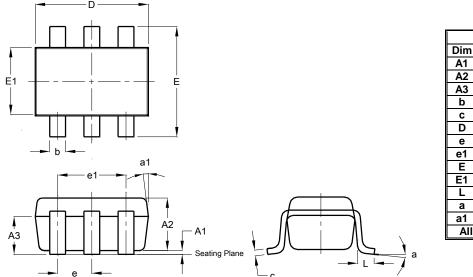
# TYPICAL CHARACTERISTICS





# **Package Outline Dimensions**

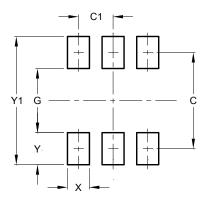
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT26							
Dim	Min	Max	Тур				
A1	0.013	0.10	0.05				
A2	1.00	1.30	1.10				
A3	0.70	0.80	0.75				
b	0.35	0.50	0.38				
С	0.10	0.20	0.15				
D	2.90	3.10	3.00				
е	-	-	0.95				
e1	-	-	1.90				
Е	2.70	3.00	2.80				
E1	1.50	1.70	1.60				
L	0.35	0.55	0.40				
а	-	-	8°				
a1	-	-	7°				
All	Dimen	sions	in mm				

# Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	2.40
C1	0.95
G	1.60
Х	0.55
Y	0.80
Y1	3.20



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